

Supporting Information

Solvothermal Synthesis, Structure and Physical Properties of $\text{Cs}[\text{Cr}(\text{en})_2M\text{Se}_4]$ ($M = \text{Ge}, \text{Sn}$) with $[\text{MSe}_4]^{4-}$ Tetrahedra as Chelating Ligand

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Table S1. Selected Bond Distances (\AA) and Angles for $\text{Cs}[\text{Cr}(\text{en})_2\text{MSe}_4]$

parameter	$M = \text{Ge}$	parameter	$M = \text{Sn}$
Cr1-N1	2.093(6)	Cr1-N1	2.091(4)
Cr1-N2	2.084(6)	Cr1-N2	2.076(5)
Cr1-N3	2.103(7)	Cr1-N3	2.112(4)
Cr1-N4	2.081(6)	Cr1-N4	2.083(5)
Cr1-Se1	2.495(1)	Cr1-Se1	2.518(1)
Cr1-Se2	2.520(1)	Cr1-Se2	2.535(1)
Ge1-Se1	2.379(1)	Sn1-Se1	2.5518(7)
Ge1-Se2	2.371(1)	Sn1-Se2	2.5340(7)
Ge1-Se3	2.319(1)	Sn1-Se3	2.5012(7)
Ge1-Se4	2.327(1)	Sn1-Se4	2.4891(7)
Cs1-Se1	3.5053(9)	Cs1-Se3	3.5506(7)
Cs1-Se2	3.5902(9)	Cs1-Se2	3.6290(7)
Cs1-Se4	3.598(1)	Cs1-Se3	3.6675(7)
Cs1-Se3	3.6228(9)	Cs1-Se1	3.7196(7)
Cs1-Se4	3.8404(8)	Cs1-Se4	3.7436(7)
Cs1-Se2	3.964(1)	Cs1-Se1	3.8181(8)
Cr1- Ge1	3.311(1)	Cr1- Sn1	3.4746(9)
Cr1-Cr1	6.065(2)	Cr1-Cr1	6.542(1)

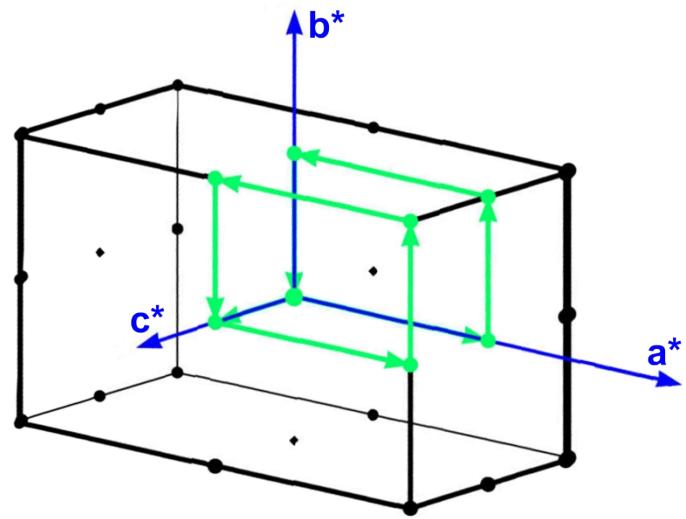


Figure S1. The Brillouin zone and k-space pathway for $\text{Cs}[\text{Cr(en)}_2\text{SnSe}_4]$

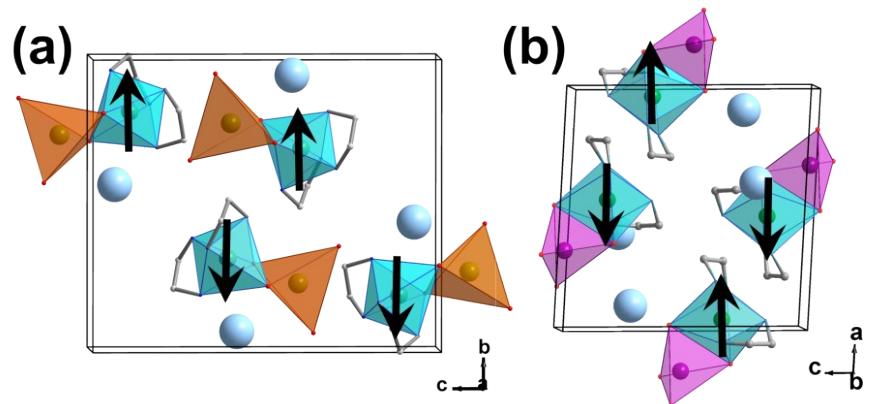


Figure S2. Schematic representations of the AFM models for the compound (a) $\text{Cs}[\text{Cr}(\text{en})_2\text{SnSe}_4]$ and (b) $\text{Cs}[\text{Cr}(\text{en})_2\text{GeSe}_4]$. (\uparrow : spin-up, \downarrow : spin-down).

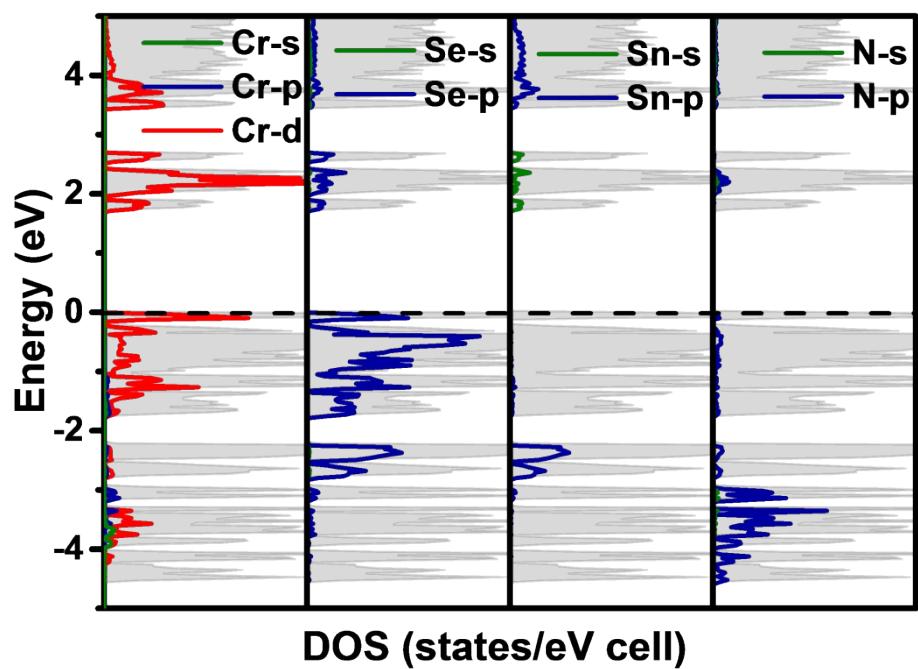


Figure S3. Partial Dos of $\text{Cs}[\text{Cr}(\text{en})_2\text{Sn}\text{Se}_4]$

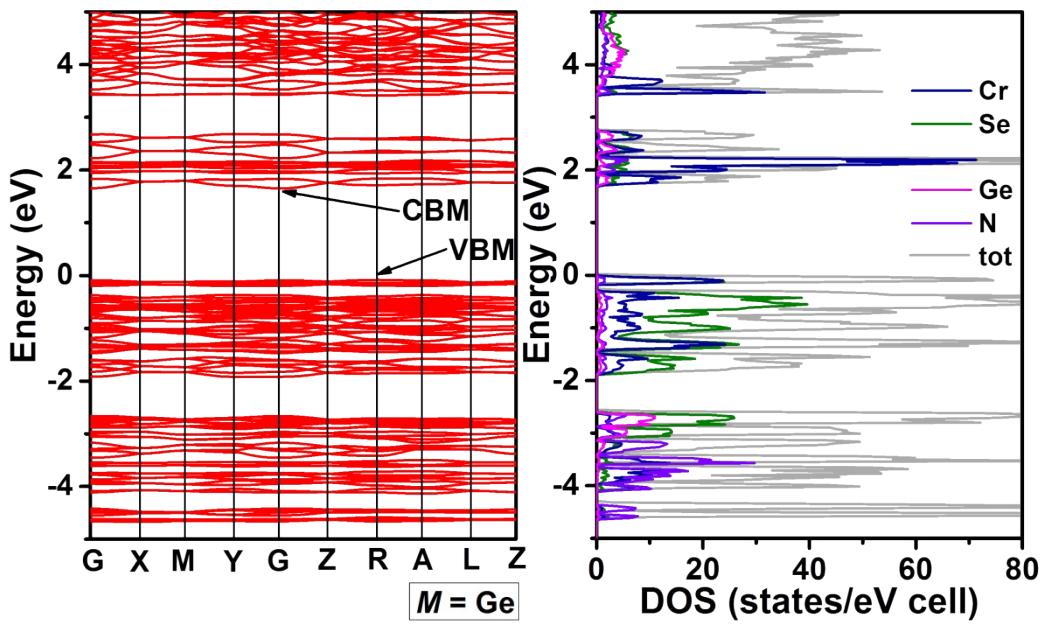


Figure S4. Calculated local electronic band structure (left) and partial density of states (right) for $\text{Cs}[\text{Cr}(\text{en})_2\text{GeSe}_4]$. (G (0, 0, 0), X (1/2, 0, 0), M (1/2, 1/2, 0), Y (0, 1/2, 0), Z (0, 0, 1/2), R (1/2, 0, 1/2), A (1/2, 1/2, 1/2), L (0, 1/2, 1/2))

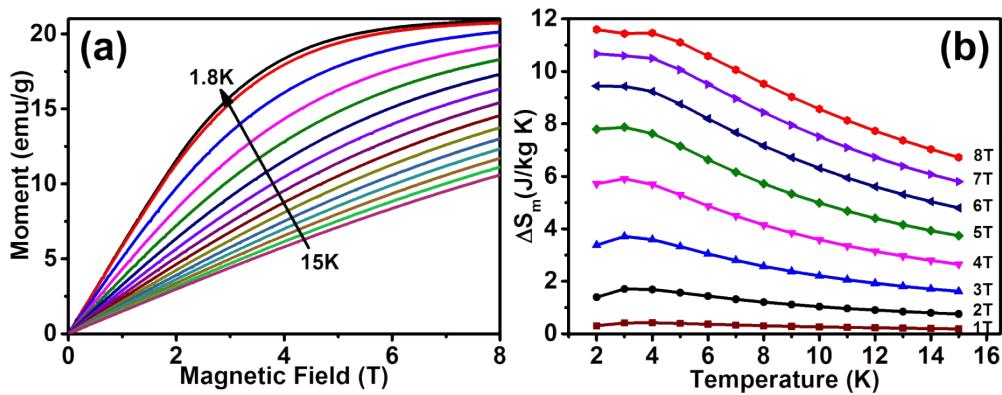


Figure S5. Magnetization *vs.* field for **1** in the temperature range of 1.8–8.2 K. (a) Field-dependent magnetization plots for $\text{Cs}[\text{Cr}(\text{en})_2\text{GeSe}_4]$ at 1.8K, 2K, 3K, 4K, 5K, 6K, 7K, 8K, 9K, 10K, 11K, 12K, 13K, 14K, and 15K. (b) ΔS_m calculated by using the magnetization data of $\text{Cs}[\text{Cr}(\text{en})_2\text{GeSe}_4]$ at different fields and temperatures.

Table S2. Magnetic Entropy Change for Selected 3d-metal Molecule-Based Magnetic

Coolants reported recently

Compound	$-\Delta S_m$ [J/kg K]	$-\Delta S_m$ [mJ/cm ³ K]	T [K]	$\mu_0 \Delta H$ [T]	Density [g/cm ³]	Ref
Cs[Cr(en) ₂ SnSe ₄] (this work)	14.2	44.0	2.0	8	3.099	
Cs[Cr(en) ₂ GeSe ₄] (this work)	11.6	33.4	2.0	8	2.884	
Mn ^{II} ₄ (N ₃) _{7.3} Cl _{0.7} (dafo) ₄	19.3	33.3	4.0	5	1.722	1
Fe ₁₄ (bta) ₆ O ₆ (OMe) ₁₈ Cl ₆	17.6	34.0	6.0	7	1.933	2
[Mn ₁₀ (OH) ₆ (amp) ₄ (ampH) ₄ I ₄ (EtOH) ₄]I ₄ ·12EtOH	17.0	26.2	5.2	7	1.543	3
[Mn ₁₄ (OH) ₂ (Hpeol) ₄ (H ₂ peol) ₆ I ₄ (EtOH) ₆]I ₄	25.0	42.5	3.8	7	1.700	3
Fe ₁₄ O ₆ (C ₂ H ₂ N ₃) ₆ (OMe) ₁₈ Cl ₆	20.3	37	6.0	7	1.782	4
[Mn(bpy) ₃] _{1.5} [Mn ₃₂ (thme) ₁₆ (bpy) ₂₄ (N ₃) ₁₂ (OAc) ₁₂](ClO ₄) ₁₁	18.2	25	1.6	7	1.4	5
[Fe ₁₄ (C ₂ H ₂ N ₃) ₆ O ₆ (OMe) ₁₈ Cl ₆]·4.5MeOH	20.3	42.2	6.0	7	2.079	6
Mn(glc) ₂	6.9	13.1	7.0	7	1.898	7
Mn(glc) ₂ (H ₂ O) ₂	60.3	112	1.8	7	1.857	7
Mn(Me-ip)(DMF)	42.4	66.7	3.0	8	1.572	8
Cs ₂ NaAl _{0.38} Cr _{0.62} F ₆	16.6	71.7	3.0	10	4.32	9
[CH ₃ NH ₂ CH ₃][CrMn(HCOO) ₆]	43.9	74.7	3.0	7	1.702	10
[CH ₃ NH ₃][CrMn(HCOO) ₆]	48.2	78.5	3.0	7	1.628	10

Reference:

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